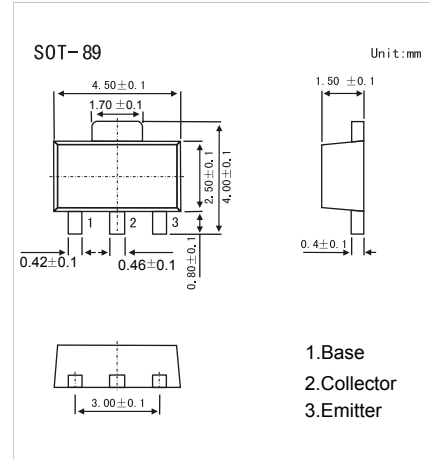


PNP Transistors

2SB1124

■ Features

- Low collector-to-emitter saturation voltage.
- Large current capacity and wide ASO.
- Fast switching speed.
- Complementary to 2SD1624



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-60	V
Collector - Emitter Voltage	V_{CE0}	-50	
Emitter - Base Voltage	V_{EB0}	-6	
Collector Current - Continuous	I_C	-3	A
Collector current -Pulse	I_{CP}	-6	
Collector Power Dissipation (Note.1)	P_C	0.5	W
		1.5	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: Mounted on ceramic board (250mm² × 0.8mm)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}, I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}, R_{BE} = \infty$	-50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}, I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2 \text{ A}, I_B = -100\text{mA}$		-0.35	-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2 \text{ A}, I_B = -100\text{mA}$		-0.94	-1.2	
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -100 \text{ mA}$	100		560	
		$V_{CE} = -2\text{V}, I_C = -3 \text{ A}$	35			
Turn-ON Time	t_{on}	See specified Test Circuit.		70		ns
Storage Time	t_{stg}			450		
Fall Time	t_f			35		
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		39		μF
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -50\text{mA}$		150		MHz

■ Classification of $h_{FE}(1)$

Type	2SB1124-R	2SB1124-S	2SB1124-T	2SB1124-U
Range	100-200	140-280	200-400	280-560
Marking	BG R*	BG S*	BG T*	BG U*

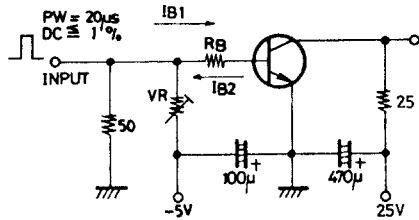


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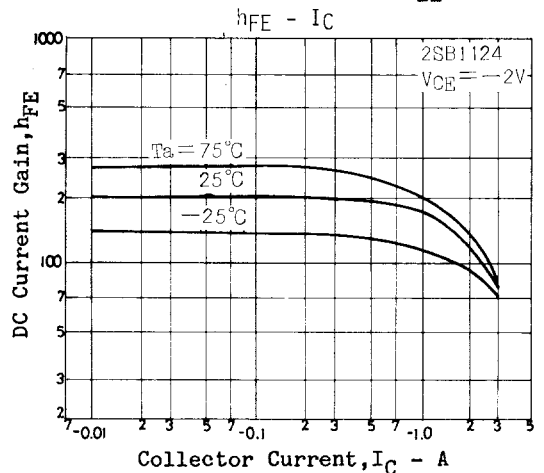
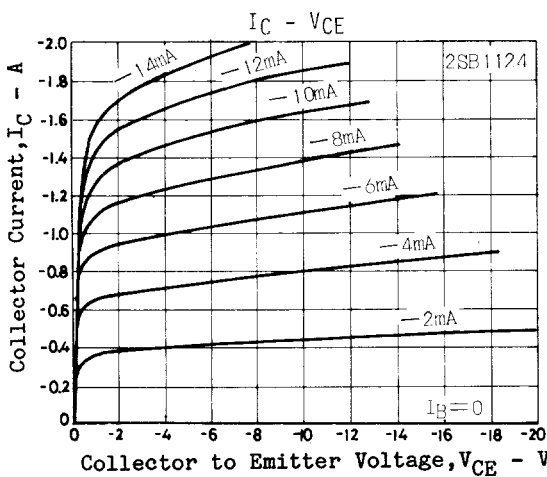
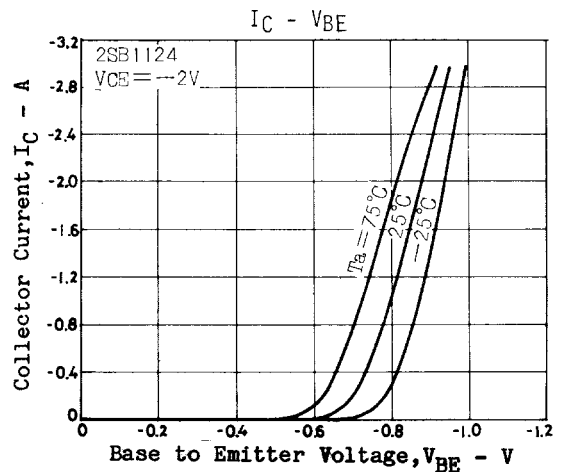
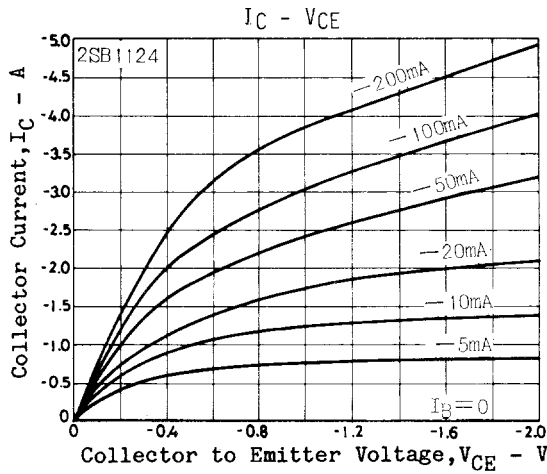
2SB1124

Switching Time Test Circuit



$10I_{B1} = -10I_{B2} = I_C = 1A$
 (For PNP, the polarity is reversed.)
 Unit (resistance : Ω , capacitance : F)

Typical Characteristics





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Typical Characteristics

